

L Number	Hits	Search Text	DB	Time stamp
4	42	("3214315" "3396401" "3419321" "3874240" "3945318" "4159414" "4309224" "4339285" "4372989" "4496607" "4539251" "4565712" "4620264" "4624934" "4663826" "4761339" "4791239" "4840853" "4847138" "4860442" "4880770" "4912087" "4924033" "4950558" "4988564" "5015618" "5055967" "5145741" "5180440" "5391841" "5459098" "5493096" "5629532" "5695828" "5733609" "5837607" "5847418" "5889234" "6025609" "6054375" "6255671" "6271576").PN.	USPAT	2004/09/29 11:09
5	0	6670693.URPN.	USPAT	2004/09/29 12:38
9	2	6271576.URPN.	USPAT	2004/09/29 12:48
13	2	("3419321" "5493096").PN.	USPAT	2004/09/29 12:50
14	4	5837607.URPN.	USPAT	2004/09/29 12:51
15	4	6025609.URPN.	USPAT	2004/09/29 12:52
16	3	("5629532" "5837607" "5847418").PN.	USPAT	2004/09/29 12:54
19	3	6054375.URPN.	USPAT	2004/09/29 12:57
22	267	((438/237).CCLS. (438/328).CCLS. (438/335).CCLS. (438/378).CCLS. (438/380).CCLS. (438/535).CCLS. (438/667).CCLS.) and laser	USPAT; US-PGPUB	2004/09/29 14:17
24	498	laser near2 synthesi\$6	EPO; JPO; DERWENT; IBM_TDB	2004/09/29 14:05
29	1399	438/237.ccls. 438/328.ccls. 438/335.ccls. 438/378.ccls. 438/380.ccls. 438/535.ccls. 438/667.ccls. 438/681.ccls.	USPAT; US-PGPUB	2004/09/29 14:17
31	4	(438/237.ccls. 438/328.ccls. 438/335.ccls. 438/378.ccls. 438/380.ccls. 438/535.ccls. 438/667.ccls. 438/681.ccls.) and	USPAT; US-PGPUB	2004/09/29 14:18
28	10	(laser near2 synthesi\$6) and ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride) mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic bandgap (band adj gap))	EPO; JPO; DERWENT; IBM_TDB	2004/09/29 14:32
27	226	(laser near2 synthesi\$6) and ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride) mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic bandgap (band adj gap))	USPAT; US-PGPUB	2004/09/29 14:26
32	943	laser same ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride) bandgap (band adj gap)) same (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic)	USPAT; US-PGPUB	2004/09/29 14:40
35	231	laser and ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride) bandgap (band adj gap)) and (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic)	EPO; JPO; DERWENT; IBM_TDB	2004/09/29 15:52
33	5	(438/237.ccls. 438/328.ccls. 438/335.ccls. 438/378.ccls. 438/380.ccls. 438/535.ccls. 438/667.ccls. 438/681.ccls.) and (laser same ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride) bandgap (band adj gap)) same (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic))	USPAT; US-PGPUB	2004/09/29 14:41
34	36	laser same ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride)) same (bandgap (band adj gap)) same (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic)	USPAT; US-PGPUB	2004/09/29 15:47

36	14	laser and ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride)) and (bandgap (band adj gap)) and (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic)	EPO; JPO; DERWENT; IBM_TDB	2004/09/29 15:52
38	47	laser and ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride)) and (diode transistor fet bjt bipolar m?sfet) and (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic)	EPO; JPO; DERWENT; IBM_TDB	2004/09/29 15:57
30	331	(438/237.ccls. 438/328.ccls. 438/335.ccls. 438/378.ccls. 438/380.ccls. 438/535.ccls. 438/667.ccls. 438/681.ccls.) and laser	USPAT; US-PGPUB	2004/09/29 16:08
37	185	laser same ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride)) same (diode transistor fet bjt bipolar m?sfet) same (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic)	USPAT; US-PGPUB	2004/09/29 16:59
-	3	6670693.pn. 6271576.pn. 5837607.pn.	USPAT; US-PGPUB	2004/09/28 18:21